Rainer Waser

List of Publications by Year
in descending order

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726 papers	49,379 citations	2213 99 h-index	2330 199 g-index
738 all docs	738 docs citations	738 times ranked	22164 citing authors

#	Article	IF	Citations
1	Memristively programmable transistors. Nanotechnology, 2022, 33, 045203.	1.3	1
2	Stabilizing amplifier with a programmable load line for characterization of nanodevices with negative differential resistance. Review of Scientific Instruments, 2022, 93, 024705.	0.6	3
3	Application of the Quantum-Point-Contact Formalism to Model the Filamentary Conduction in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Ta</mml:mi></mml:math> <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi /><mml:mn>2</mml:mn></mml:msub></mml:math> <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>n</mml:mi>	1.5	5
4	Effect of the Threshold Kinetics on the Filament Relaxation Behavior of Agâ€Based Diffusive Memristors. Advanced Functional Materials, 2022, 32, .	7.8	33
5	Oxygen Diffusion in Platinum Electrodes: A Molecular Dynamics Study of the Role of Extended Defects. Advanced Materials Interfaces, 2022, 9, .	1.9	7
6	Reliability aspects of binary vector-matrix-multiplications using ReRAM devices. Neuromorphic Computing and Engineering, 2022, 2, 034001.	2.8	14
7	NEUROTEC I: Neuro-inspired Artificial Intelligence Technologies for the Electronics of the Future. , 2022, , .		0
8	Tradeâ€Off Between Data Retention and Switching Speed in Resistive Switching ReRAM Devices. Advanced Electronic Materials, 2021, 7, 2000815.	2.6	20
9	Comments on ``Experimental Demonstration of Memristor-Aided Logic (MAGIC) Using Valence Change Memory (VCM)''. IEEE Transactions on Electron Devices, 2021, , 1-1.	1.6	0
10	Carbonate formation lowers the electrocatalytic activity of perovskite oxides for water electrolysis. Journal of Materials Chemistry A, 2021, 9, 19940-19948.	5.2	11
11	Tuning electrochemically driven surface transformation in atomically flat LaNiO3 thin films for enhanced water electrolysis. Nature Materials, 2021, 20, 674-682.	13.3	105
12	Impact of the Ohmic Electrode on the Endurance of Oxide-Based Resistive Switching Memory. IEEE Transactions on Electron Devices, 2021, 68, 1024-1030.	1.6	26
13	Current-limiting amplifier for high speed measurement of resistive switching data. Review of Scientific Instruments, 2021, 92, 054701.	0.6	12
14	Utilizing the Switching Stochasticity of HfO2/TiOx-Based ReRAM Devices and the Concept of Multiple Device Synapses for the Classification of Overlapping and Noisy Patterns. Frontiers in Neuroscience, 2021, 15, 661856.	1.4	26
15	Determining the Electrical Charging Speed Limit of ReRAM Devices. IEEE Journal of the Electron Devices Society, 2021, 9, 667-678.	1.2	11
16	Standards for the Characterization of Endurance in Resistive Switching Devices. ACS Nano, 2021, 15, 17214-17231.	7.3	128
17	Intrinsic RESET Speed Limit of Valence Change Memories. ACS Applied Electronic Materials, 2021, 3, 5563-5572.	2.0	15
18	Effect of Cationic Interface Defects on Band Alignment and Contact Resistance in Metal/Oxide Heterojunctions. Advanced Electronic Materials, 2020, 6, 1900808.	2.6	9

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19	HRS Instability in Oxide-Based Bipolar Resistive Switching Cells. IEEE Transactions on Electron Devices, 2020, 67, 4208-4215.	1.6	32
20	Comprehensive model for the electronic transport in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mtext>Pt/SrTi</mml:mtext><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> analog memristive devices. Physical Review B, 2020, 102, .	1.1	20
21	Variability-Aware Modeling of Filamentary Oxide-Based Bipolar Resistive Switching Cells Using SPICE Level Compact Models. IEEE Transactions on Circuits and Systems I: Regular Papers, 2020, 67, 4618-4630.	3.5	72
22	Inâ€Memory Binary Vectorâ€“Matrix Multiplication Based on Complementary Resistive Switches. Advanced Intelligent Systems, 2020, 2, 2000134.	3.3	9
23	Design of defect-chemical properties and device performance in memristive systems. Science Advances, 2020, 6, eaaz9079.	4.7	65
24	Study of the SET switching event of VCM-based memories on a picosecond timescale. Journal of Applied Physics, 2020, 127, .	1.1	20
25	Experimental Demonstration of Memristor-Aided Logic (MAGIC) Using Valence Change Memory (VCM). IEEE Transactions on Electron Devices, 2020, 67, 3115-3122.	1.6	58
26	Emerging materials in neuromorphic computing: Guest editorial. APL Materials, 2020, 8, .	2.2	16
27	Defect chemistry of donor-doped BaTiO₃ with BaO-excess for reduction resistant PTCR thermistor applications â€“ redox-behaviour. Physical Chemistry Chemical Physics, 2020, 22, 8219-8232.	1.3	10
28	On the universality of the Iâ€“V switching characteristics in non-volatile and volatile resistive switching oxides. Faraday Discussions, 2019, 213, 183-196.	1.6	18
29	Topotactic Phase Transition Driving Memristive Behavior. Advanced Materials, 2019, 31, e1903391.	11.1	61
30	Mott-transition-based RRAM. Materials Today, 2019, 28, 63-80.	8.3	56
31	Mechanism of memristive switching in OxRAM. , 2019, , 137-170.		7
32	Stateful Three-Input Logic with Memristive Switches. Scientific Reports, 2019, 9, 14618.	1.6	44
33	Metallic filamentary conduction in valence change-based resistive switching devices: the case of TaO_x thin film with x â^¼ 1. Nanoscale, 2019, 11, 16978-16990.	2.8	16
34	Exploiting the switching dynamics of HfO2-based ReRAM devices for reliable analog memristive behavior. APL Materials, 2019, 7, .	2.2	94
35	Analyses of a 1-layer neuromorphic network using memristive devices with non-continuous resistance levels. APL Materials, 2019, 7, 091110.	2.2	8
36	Spectroscopic elucidation of ionic motion processes in tunnel oxide-based memristive devices. Faraday Discussions, 2019, 213, 215-230.	1.6	13

#	Article	IF	Citations
37	Valence change ReRAMs (VCM) - Experiments and modelling: general discussion. Faraday Discussions, 2019, 213, 259-286.	1.6	2
38	Electrochemical metallization ReRAMs (ECM) - Experiments and modelling: general discussion. Faraday Discussions, 2019, 213, 115-150.	1.6	5
39	Phase-change memories (PCM) â€“ Experiments and modelling: general discussion. Faraday Discussions, 2019, 213, 393-420.	1.6	7
40	Compact Modeling of Complementary Switching in Oxide-Based ReRAM Devices. IEEE Transactions on Electron Devices, 2019, 66, 1268-1275.	1.6	39
41	Heavily donor-doped, optically translucent ferroelectric barium titanate ceramics through defect chemical engineering. CrystEngComm, 2019, 21, 2854-2862.	1.3	4
42	Introduction to new memory paradigms: memristive phenomena and neuromorphic applications. Faraday Discussions, 2019, 213, 11-27.	1.6	35
43	Electric transport properties of rare earth doped YbxCa1-xMnO3 ceramics (part I: Optimization of) Tj ETQq1 1 0.784314 rgBT /Overlock	2.8	3
44	In-Gap States and Band-Like Transport in Memristive Devices. Nano Letters, 2019, 19, 54-60.	4.5	22
45	Chemical control of the electrical surface properties in donor-doped transition metal oxides. Physical Review Materials, 2019, 3, .	0.9	15
46	Electrically controlled transformation of memristive titanates into mesoporous titanium oxides via incongruent sublimation. Scientific Reports, 2018, 8, 3774.	1.6	12
47	Valence change detection in memristive oxide based heterostructure cells by hard X-ray photoelectron emission spectroscopy. APL Materials, 2018, 6, .	2.2	15
48	Different threshold and bipolar resistive switching mechanisms in reactively sputtered amorphous undoped and Cr-doped vanadium oxide thin films. Journal of Applied Physics, 2018, 123, .	1.1	33
49	ReRAM: Role of the Electrode Material on the RESET Limitation in Oxide ReRAM Devices (Adv. Electron.) Tj ETQq1 1 0.784314 rgBT /Over	2.6	2
50	Role of the Electrode Material on the RESET Limitation in Oxide ReRAM Devices. Advanced Electronic Materials, 2018, 4, 1700243.	2.6	20
51	Multi-valued and Fuzzy Logic Realization using TaOx Memristive Devices. Scientific Reports, 2018, 8, 8.	1.6	135
52	Nanoarchitectonics for Controlling the Number of Dopant Atoms in Solid Electrolyte Nanodots. Advanced Materials, 2018, 30, 1703261.	11.1	59
53	Degradation Kinetics during Oxygen Electrocatalysis on Perovskite-Based Surfaces in Alkaline Media. Langmuir, 2018, 34, 1347-1352.	1.6	18
54	Processes and Effects of Oxygen and Moisture in Resistively Switching TaO_x and HfO_x. Advanced Electronic Materials, 2018, 4, 1700458.	2.6	85

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55	Atomistic Investigation of the Schottky Contact Conductance Limits at SrTiO3 based Resistive Switching Devices. , 2018, , .		2
56	The influence of interfacial (sub)oxide layers on the properties of pristine resistive switching devices. , 2018, , .		2
57	Field-Driven Hopping Transport of Oxygen Vacancies in Memristive Oxide Switches with Interface-Mediated Resistive Switching. Physical Review Applied, 2018, 10, .	1.5	34
58	Addressing Multiple Resistive States of Polyoxovanadates: Conductivity as a Function of Individual Molecular Redox States. Journal of the American Chemical Society, 2018, 140, 16635-16640.	6.6	49
59	Self-limited single nanowire systems combining all-in-one memristive and neuromorphic functionalities. Nature Communications, 2018, 9, 5151.	5.8	115
60	Nanospectroscopy of Infrared Phonon Resonance Enables Local Quantification of Electronic Properties in Doped SrTiO₃ Ceramics. Advanced Functional Materials, 2018, 28, 1802834.	7.8	32
61	Crossover From Deterministic to Stochastic Nature of Resistive-Switching Statistics in a Tantalum Oxide Thin Film. IEEE Transactions on Electron Devices, 2018, 65, 4320-4325.	1.6	10
62	Correlation between the transport mechanisms in conductive filaments inside Ta2O5-based resistive switching devices and in substoichiometric TaOx thin films. Applied Physics Letters, 2018, 112, .	1.5	19
63	Improved Switching Stability and the Effect of an Internal Series Resistor in HfO₂/TiO_{<italic>x</italic>} Bilayer ReRAM Cells. IEEE Transactions on Electron Devices, 2018, 65, 3229-3236.	1.6	95
64	Reduction of the forming voltage through tailored oxygen non-stoichiometry in tantalum oxide ReRAM devices. Scientific Reports, 2018, 8, 10861.	1.6	43
65	Understanding the Coexistence of Two Bipolar Resistive Switching Modes with Opposite Polarity in Pt/TiO₂/Ti/Pt Nanosized ReRAM Devices. ACS Applied Materials & Interfaces, 2018, 10, 29766-29778.	4.0	71
66	A Theoretical and Experimental View on the Temperature Dependence of the Electronic Conduction through a Schottky Barrier in a Resistively Switching SrTiO₃â€Based Memory Cell. Advanced Electronic Materials, 2018, 4, 1800062.	2.6	31
67	Oxygen Exchange Processes between Oxide Memristive Devices and Water Molecules. Advanced Materials, 2018, 30, e1800957.	11.1	57
68	Resistive switching in optoelectronic III-V materials based on deep traps. Scientific Reports, 2018, 8, 9483.	1.6	2
69	A SIMS study of cation and anion diffusion in tantalum oxide. Physical Chemistry Chemical Physics, 2018, 20, 989-996.	1.3	21
70	Field-enhanced route to generating anti-Frenkel pairs in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>HfO</mml:mi><mml:mn>2</mml:mn></mml:msub></mm Physical Review Materials, 2018, 2, .	0.9	32
71	Structure and orbital ordering of ultrathin LaVO3probed by atomic resolution electron microscopy and Raman spectroscopy. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1600350.	1.2	4
72	Coexistence of Grainâ€Boundariesâ€Assisted Bipolar and Threshold Resistive Switching in Multilayer Hexagonal Boron Nitride. Advanced Functional Materials, 2017, 27, 1604811.	7.8	229

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73	Energy Level Alignment at the Fullerene/Titanium Oxide Ultrathin Film Interface. Journal of Physical Chemistry C, 2017, 121, 2815-2821.	1.5	4
74	3-bit Resistive RAM Write-Read Scheme Based on Complementary Switching Mechanism. IEEE Electron Device Letters, 2017, 38, 449-452.	2.2	20
75	Ion migration in crystalline and amorphous HfOX. Journal of Chemical Physics, 2017, 146, .	1.2	45
76	SET kinetics of electrochemical metallization cells: influence of counter-electrodes in SiO₂/Ag based systems. Nanotechnology, 2017, 28, 135205.	1.3	55
77	Anomalous Resistance Hysteresis in Oxide ReRAM: Oxygen Evolution and Reincorporation Revealed by In Situ TEM. Advanced Materials, 2017, 29, 1700212.	11.1	166
78	Thin film proton conducting membranes for micro-solid oxide fuel cells by chemical solution deposition. Thin Solid Films, 2017, 636, 446-457.	0.8	11
79	Interface-driven formation of a two-dimensional dodecagonal fullerene quasicrystal. Nature Communications, 2017, 8, 15367.	5.8	16
80	Overcoming the RESET Limitation in Tantalum Oxide-Based ReRAM Using an Oxygen-Blocking Layer. , 2017, , .		1
81	Oxygen partial pressure dependence of surface space charge formation in donor-doped SrTiO₃. APL Materials, 2017, 5, 056106.	2.2	21
82	Nanosized Conducting Filaments Formed by Atomic-Scale Defects in Redox-Based Resistive Switching Memories. Chemistry of Materials, 2017, 29, 3164-3173.	3.2	70
83	Thermodynamic Ground States of Complex Oxide Heterointerfaces. ACS Applied Materials & Interfaces, 2017, 9, 1086-1092.	4.0	34
84	Improvement of SET variability in TaO_xbased resistive RAM devices. Nanotechnology, 2017, 28, 465203.	1.3	8
85	Electrochemical Tantalum Oxide for Resistive Switching Memories. Advanced Materials, 2017, 29, 1703357.	11.1	69
86	Spectroscopic Indications of Tunnel Barrier Charging as the Switching Mechanism in Memristive Devices. Advanced Functional Materials, 2017, 27, 1702282.	7.8	29
87	Volatile HRS asymmetry and subloops in resistive switching oxides. Nanoscale, 2017, 9, 14414-14422.	2.8	11
88	Design rules for threshold switches based on a field triggered thermal runaway mechanism. Journal of Computational Electronics, 2017, 16, 1175-1185.	1.3	10
89	Ordering and Phase Control in Epitaxial Double-Perovskite Catalysts for the Oxygen Evolution Reaction. ACS Catalysis, 2017, 7, 7029-7037.	5.5	35
90	Investigation of the Impact of High Temperatures on the Switching Kinetics of Redoxâ€Based Resistive Switching Cells using a Highâ€Speed Nanoheater. Advanced Electronic Materials, 2017, 3, 1700294.	2.6	41

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91	Interaction between depolarization effects, interface layer, and fatigue behavior in PZT thin film capacitors. Journal of Applied Physics, 2017, 122, .	1.1	11
92	Understanding on the selective carbon monoxide sensing characteristics of copper oxide-zinc oxide composite thin films. Sensors and Actuators B: Chemical, 2017, 253, 685-696.	4.0	26
93	Subfilamentary Networks Cause Cycle-to-Cycle Variability in Memristive Devices. ACS Nano, 2017, 11, 6921-6929.	7.3	95
94	Physical modeling of the electroforming process in resistive-switching devices. , 2017, , .		12
95	Thermal effects on the I-V characteristics of filamentary VCM based ReRAM-cells using a nanometer-sized heater. , 2017, , .		2
96	Threshold Switching in Amorphous Cr-Doped Vanadium Oxide for New Crossbar Selector. , 2016, , .		8
97	Multidimensional Simulation of Threshold Switching in NbO₂ Based on an Electric Field Triggered Thermal Runaway Model. Advanced Electronic Materials, 2016, 2, 1600169.	2.6	95
98	Dependence of the SET switching variability on the initial state in HfO_xâ€based ReRAM. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 316-319.	0.8	19
99	Resistance switching behavior of atomic layer deposited SrTiO3 film through possible formation of Sr2Ti6O13 or Sr1Ti11O20 phases. Scientific Reports, 2016, 6, 20550.	1.6	17
100	The influence of non-stoichiometry on the switching kinetics of strontium-titanate ReRAM devices. Journal of Applied Physics, 2016, 120, .	1.1	9
101	Probing orbital ordering in LaVO3 epitaxial films by Raman scattering. APL Materials, 2016, 4, .	2.2	11
102	Resistive Switching in Aqueous Nanopores by Shock Electrodeposition. Electrochimica Acta, 2016, 222, 370-375.	2.6	10
103	Forming-free metal-oxide ReRAM by oxygen ion implantation process. , 2016, , .		13
104	Homogeneity and variation of donor doping in Verneuil-grown SrTiO3:Nb single crystals. Scientific Reports, 2016, 6, 32250.	1.6	29
105	Hafnium carbide formation in oxygen deficient hafnium oxide thin films. Applied Physics Letters, 2016, 108, .	1.5	7
106	Verification of redox-processes as switching and retention failure mechanisms in Nb:SrTiO₃/metal devices. Nanoscale, 2016, 8, 13967-13975.	2.8	65
107	Synthesis of nitrogen and lanthanum codoped barium titanate with a novel thermal ammonolysis reactor. Journal of the European Ceramic Society, 2016, 36, 2719-2725.	2.8	3
108	Nanoionic Resistive Switching Memories: On the Physical Nature of the Dynamic Reset Process. Advanced Electronic Materials, 2016, 2, 1500233.	2.6	141

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109	Hydroxyl Defect Effect on Reoxidation of Scâ€Doped (Ba , Ca)(Ti , Zr) O 3 Fired in Reducing Atmospheres. Journal of the American Ceramic Society, 2016, 99, 1311-1317.	1.9	10
110	Hydroxyl defect effect on the resistance degradation behavior in Y-doped (Ba,Ca)(Ti,Zr)O 3 bulk ceramics. Journal of the European Ceramic Society, 2016, 36, 3147-3155.	2.8	4
111	Dynamics of the metal-insulator transition of donor-doped<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>SrTi</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2016, 94, .	1.1	46
112	(Invited) Mobile Ions, Transport and Redox Processes in Memristive Devices. ECS Transactions, 2016, 75, 27-39.	0.3	13
113	Stability and Degradation of Perovskite Electrocatalysts for Oxygen Evolution Reaction. Electrochimica Acta, 2016, 218, 156-162.	2.6	29
114	Ultrafast switching in Ta<inf>2</inf>O<inf>5</inf>-based resistive memories. , 2016, , .		9
115	Energy efficient computing by redox-based memristive oxide elements. , 2016, , .		1
116	Impact of oxygen exchange reaction at the ohmic interface in Ta₂O₅-based ReRAM devices. Nanoscale, 2016, 8, 17774-17781.	2.8	116
117	Space charges and defect concentration profiles at complex oxide interfaces. Physical Review B, 2016, 93, .	1.1	51
118	Multistate Memristive Tantalum Oxide Devices for Ternary Arithmetic. Scientific Reports, 2016, 6, 36652.	1.6	58
119	Quantifying redox-induced Schottky barrier variations in memristive devices via in operando spectromicroscopy with graphene electrodes. Nature Communications, 2016, 7, 12398.	5.8	87
120	Energy dissipation during pulsed switching of strontium-titanate based resistive switching memory devices. , 2016, , .		6
121	A 2D axisymmetric dynamic drift-diffusion model for numerical simulation of resistive switching phenomena in metal oxides. , 2016, , .		12
122	Simulation of threshold switching based on an electric field induced thermal runaway. , 2016, , .		3
123	Humidity effects on the redox reactions and ionic transport in a Cu/Ta₂O₅/Pt atomic switch structure. Japanese Journal of Applied Physics, 2016, 55, 06GJ09.	0.8	49
124	Realization of Minimum and Maximum Gate Function in Ta2O5-based Memristive Devices. Scientific Reports, 2016, 6, 23967.	1.6	32
125	Internal Cell Resistance as the Origin of Abrupt Reset Behavior in HfO2-Based Devices Determined from Current Compliance Series. , 2016, , .		13
126	Tuning the surface electronic structure of a Pt₃Ti(111) electro catalyst. Nanoscale, 2016, 8, 13924-13933.	2.8	17

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127	3-Bit Multilevel Switching by Deep Reset Phenomenon in Pt/W/TaO_X/Pt-ReRAM Devices. IEEE Electron Device Letters, 2016, 37, 564-567.	2.2	58
128	Nonlinearity analysis of TaOX redox-based RRAM. Microelectronic Engineering, 2016, 154, 38-41.	1.1	14
129	Pr_xBa_{1-x}CoO₃Oxide Electrodes for Oxygen Evolution Reaction in Alkaline Solutions by Chemical Solution Deposition. Journal of the Electrochemical Society, 2016, 163, F166-F170.	1.3	20
130	Resistive Switching Mechanisms on TaO_x and SrRuO₃ Thin-Film Surfaces Probed by Scanning Tunneling Microscopy. ACS Nano, 2016, 10, 1481-1492.	7.3	100
131	Nanoscale cation motion in TaOx, HfOx and TiOx memristive systems. Nature Nanotechnology, 2016, 11, 67-74.	15.6	524
132	Formation and Movement of Cationic Defects During Forming and Resistive Switching in SrTiO₃ Thin Film Devices. Advanced Functional Materials, 2015, 25, 6360-6368.	7.8	56
133	Redox Reactions at Cu,Ag/Ta₂O₅ Interfaces and the Effects of Ta₂O₅ Film Density on the Forming Process in Atomic Switch Structures. Advanced Functional Materials, 2015, 25, 6374-6381.	7.8	148
134	Resistively Switching Chalcogenides. Advanced Functional Materials, 2015, 25, 6285-6286.	7.8	11
135	Realization of Boolean Logic Functionality Using Redoxâ€Based Memristive Devices. Advanced Functional Materials, 2015, 25, 6414-6423.	7.8	127
136	A HfO₂â€Based Complementary Switching Crossbar Adder. Advanced Electronic Materials, 2015, 1, 1500138.	2.6	51
137	Resistive Switching of Individual, Chemically Synthesized TiO₂Nanoparticles. Small, 2015, 11, 6444-6456.	5.2	24
138	Avalancheâ€Dischargeâ€Induced Electrical Forming in Tantalum Oxideâ€Based Metalâ€“Insulatorâ€“Metal Structures. Advanced Functional Materials, 2015, 25, 7154-7162.	7.8	28
139	Enhanced fullereneâ€“Au(111) coupling in (2âˆš3 Ã— 2âˆš3)R30Â° superstructures with intermolecular interactions. Beilstein Journal of Nanotechnology, 2015, 6, 1421-1431.	1.5	16
140	Modeling of Quantized Conductance Effects in Electrochemical Metallization Cells. IEEE Nanotechnology Magazine, 2015, 14, 505-512.	1.1	33
141	Controllability of multi-level states in memristive device models using a transistor as current compliance during SET operation. , 2015, , .		0
142	Impedance spectroscopy study of the unipolar and bipolar resistive switching states of atomic layer deposited polycrystalline ZrO₂ thin films. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 751-766.	0.8	20
143	A Complementary Resistive Switch-Based Crossbar Array Adder. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2015, 5, 64-74.	2.7	100
144	Understanding the conductive channel evolution in Na:WO₃â^'x<sub>-based planar devices. Nanoscale, 2015, 7, 6023-6030.	2.8	15

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145	The influence of the local oxygen vacancy concentration on the piezoresponse of strontium titanate thin films. Nanoscale, 2015, 7, 14351-14357.	2.8	30
146	Understanding filamentary growth in electrochemical metallization memory cells using kinetic Monte Carlo simulations. Nanoscale, 2015, 7, 12673-12681.	2.8	85
147	Atomic structure and chemistry of dislocation cores at low-angle tilt grain boundary in SrTiO3 bicrystals. Acta Materialia, 2015, 89, 344-351.	3.8	58
148	Effect of RESET Voltage on Distribution of SET Switching Time of Bipolar Resistive Switching in a Tantalum Oxide Thin Film. IEEE Transactions on Electron Devices, 2015, 62, 1561-1567.	1.6	24
149	Study of Memristive Associative Capacitive Networks for CAM Applications. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2015, 5, 153-161.	2.7	9
150	Low-current operations in 4F²-compatible Ta₂O₅-based complementary resistive switches. Nanotechnology, 2015, 26, 415202.	1.3	20
151	Spectromicroscopic insights for rational design of redox-based memristive devices. Nature Communications, 2015, 6, 8610.	5.8	100
152	Phase-Change and Redox-Based Resistive Switching Memories. Proceedings of the IEEE, 2015, 103, 1274-1288.	16.4	142
153	Physical simulation of dynamic resistive switching in metal oxides using a Schottky contact barrier model. , 2015, , .		21
154	Processes and Limitations during Filament Formation and Dissolution in GeS_x-based ReRAM Memory Cells. Journal of Physical Chemistry C, 2015, 119, 18678-18685.	1.5	20
155	In-memory adder functionality in 1S1R arrays. , 2015, , .		16
156	Critical ReRAM Stack Parameters Controlling Complimentary versus Bipolar Resistive Switching. , 2015, , .		13
157	Transport limits in defect-engineered LaAlO₃/SrTiO₃ bilayers. Nanoscale, 2015, 7, 1013-1022.	2.8	39
158	On the SET/RESET current asymmetry in electrochemical metallization memory cells. Physica Status Solidi - Rapid Research Letters, 2014, 8, 540-544.	1.2	13
159	Origin of the SET Kinetics of the Resistive Switching in Tantalum Oxide Thin Films. IEEE Electron Device Letters, 2014, 35, 259-261.	2.2	47
160	Nanobattery Effect in RRAMsâ€"Implications on Device Stability and Endurance. IEEE Electron Device Letters, 2014, 35, 208-210.	2.2	56
161	(Keynote) Atomic Scale and Interface Interactions in Redox-Based Resistive Switching Memories. ECS Transactions, 2014, 64, 3-18.	0.3	8
162	Quantum size effects and non-equilibrium states in nanoscale silicon dioxide based resistive switches. , 2014, , .		2

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163	An experimental associative capacitive network based on complementary resistive switches for memory-intensive computing. , 2014, , .		2
164	Fast mapping of inhomogeneities in the popular metallic perovskite Nb:SrTiO₃by confocal Raman microscopy. Physica Status Solidi - Rapid Research Letters, 2014, 08, 781-784.	1.2	7
165	Statistical modeling of electrochemical metallization memory cells. , 2014, , .		4
166	Directed Immobilization of Janus-AuNP in Heterometallic Nanogaps: a Key Step Toward Integration of Functional Molecular Units in Nanoelectronics. Journal of Physical Chemistry C, 2014, 118, 27142-27149.	1.5	16
167	Impact of the Counterâ€Electrode Material on Redox Processes in Resistive Switching Memories. ChemElectroChem, 2014, 1, 1287-1292.	1.7	78
168	Simulation of TaO<inf>x</inf>-based complementary resistive switches by a physics-based memristive model. , 2014, , .		33
169	Chemical solution deposition of ferroelectric yttrium-doped hafnium oxide films on platinum electrodes. Applied Physics Letters, 2014, 104, .	1.5	134
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